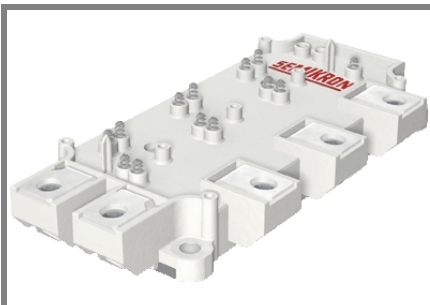


SEMiX 71GD12T4s



SEMiX® 13s

Trench IGBT Modules

SEMiX 71GD12T4s

Target Data

Features

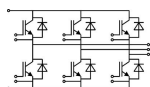
- Homogeneous Si
- Trench = Trenchgate technology
- $V_{CE(sat)}$ with positive temperature coefficient
- High short circuit capability

Typical Applications

- AC inverter drives
- UPS
- Electronic Welding

Remarks

- Case temperature limited to $T_C=125^\circ\text{C}$ max.
- Product reliability results are valid for $T_j=150^\circ\text{C}$

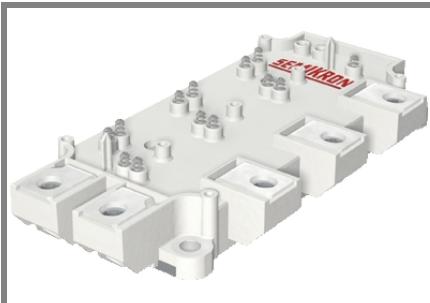


GD

Absolute Maximum Ratings		$T_{case} = 25^\circ\text{C}$, unless otherwise specified		
Symbol	Conditions	Values	Units	
IGBT				
V_{CES}	$T_j = 25^\circ\text{C}$	1200	V	
I_C	$T_j = 175^\circ\text{C}$	$T_c = 25^\circ\text{C}$	115	A
		$T_c = 80^\circ\text{C}$	90	A
I_{CRM}	$I_{CRM} = 3 \times I_{Cnom}$	225	A	
V_{GES}		± 20	V	
t_{psc}	$V_{CC} = 600\text{ V}; V_{GE} \leq 20\text{ V}; T_j = 150^\circ\text{C}$ $V_{CES} < 1200\text{ V}$	10	μs	
Inverse Diode				
I_F	$T_j = 175^\circ\text{C}$	$T_c = 25^\circ\text{C}$	95	A
		$T_c = 80^\circ\text{C}$	75	A
I_{FRM}	$I_{FRM} = 3 \times I_{Fnom}$	225	A	
Module				
$I_{t(RMS)}$		600	A	
T_{vj}		- 40 ... + 175	$^\circ\text{C}$	
T_{stg}		- 40 ... + 125	$^\circ\text{C}$	
V_{isol}	AC, 1 min.	4000	V	

Characteristics		$T_{case} = 25^\circ\text{C}$, unless otherwise specified			
Symbol	Conditions	min.	typ.	max.	Units
IGBT					
$V_{GE(th)}$	$V_{GE} = V_{CE}, I_C = 3\text{ mA}$	5	5,8	6,5	V
I_{CES}	$V_{GE} = 0\text{ V}, V_{CE} = V_{CES}$				$T_j = 25^\circ\text{C}$ mA
V_{CE0}					$T_j = 25^\circ\text{C}$
					$T_j = 150^\circ\text{C}$
r_{CE}	$V_{GE} = 15\text{ V}$				$T_j = 25^\circ\text{C}$
					$T_j = 150^\circ\text{C}$
$V_{CE(sat)}$	$I_{Cnom} = 75\text{ A}, V_{GE} = 15\text{ V}$				$T_j = 25^\circ\text{C}_{chiplev.}$
					$T_j = 150^\circ\text{C}_{chiplev.}$
C_{ies}	$V_{CE} = 25, V_{GE} = 0\text{ V}$	$f = 1\text{ MHz}$			4,4
C_{oes}					0,3
C_{res}					0,25
Q_G	$V_{GE} = -8 \dots +15\text{ V}$				425
R_{Gint}	$T_j = 25^\circ\text{C}$				10
$t_{d(on)}$	$R_{Gon} = \Omega$	$V_{CC} = V$	$I_{Cnom} = A$	$T_j = 150^\circ\text{C}$	8,3
t_r					
E_{on}	$R_{Goff} = \Omega$				8,3
$t_{d(off)}$					
t_f					
E_{off}					mJ
$R_{th(j-c)}$	per IGBT				0,38

SEMiX 71GD12T4s



SEMiX® 13s

Trench IGBT Modules

SEMiX 71GD12T4s

Target Data

Features

- Homogeneous Si
- Trench = Trenchgate technology
- $V_{CE(sat)}$ with positive temperature coefficient
- High short circuit capability

Typical Applications

- AC inverter drives
- UPS
- Electronic Welding

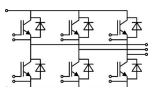
Remarks

- Case temperature limited to $T_C=125^\circ\text{C}$ max.
- Product reliability results are valid for $T_j=150^\circ\text{C}$

Characteristics			min.	typ.	max.	Units
Inverse Diode						
$V_F = V_{EC}$	$I_{Fnom} = 75 \text{ A}; V_{GE} = 0 \text{ V}$	$T_j = 25^\circ\text{C}_{\text{chiplev.}}$		2,2	2,5	V
		$T_j = 150^\circ\text{C}_{\text{chiplev.}}$		2,1	2,45	V
V_{F0}		$T_j = 25^\circ\text{C}$		1,3	1,5	V
		$T_j = 150^\circ\text{C}$		0,9	1,1	V
r_F		$T_j = 25^\circ\text{C}$		12	13,3	mΩ
		$T_j = 150^\circ\text{C}$		16	18	mΩ
I_{RRM}	$I_{Fnom} = 75 \text{ A}$	$T_j = 150^\circ\text{C}$				A
Q_{rr}						μC
E_{rr}	$V_{GE} = -15 \text{ V}; V_{CC} = 600 \text{ V}$			5,6		mJ
$R_{th(j-c)D}$	per diode				0,58	K/W
Module						
L_{CE}				20		nH
$R_{CC'+EE'}$	res., terminal-chip	$T_{case} = 25^\circ\text{C}$		0,7		mΩ
		$T_{case} = 125^\circ\text{C}$		1		mΩ
$R_{th(c-s)}$	per module			0,04		K/W
M_s	to heat sink (M5)			3	5	Nm
M_t	to terminals (M6)			2,5	5	Nm
w					350	g
Temperature sensor						
R_{100}	$T_c = 100^\circ\text{C}$ ($R_{25} = 5 \text{ k}\Omega$)			0,493±5%		kΩ
$B_{100/125}$	$R(T) = R_{100} \exp[B_{100/125} (1/T - 1/T_{100})]$; $T[\text{K}]$			3550±2%		K

This is an electrostatic discharge sensitive device (ESDS), international standard IEC 60747-1, Chapter IX.

This technical information specifies semiconductor devices but promises no characteristics. No warranty or guarantee expressed or implied is made regarding delivery, performance or suitability.



GD

